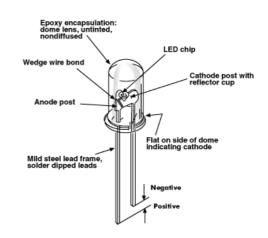
## **■** Features

- 385 nm UV-LED
- 5 mm clear epoxy package
- UV transparent resin
- Chip material based on GaN



## ■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Value	Unit	
Power Dissipation	P <sub>d</sub>	100	mW	
Continuous Forward Current	I <sub>F</sub>	25	mA	
Reverse Voltage	V <sub>R</sub>	5	V	
Operating Temperature	T <sub>opr</sub>	-20 to +80	°C	
Storage Temperature	T <sub>stg</sub>	-30 to +100	•C	
Soldering Temperature	T <sub>sol</sub> *2	280 (with in 3 seconds)	°C	

<sup>\*1</sup>  $I_{FM}$  conditions : Pulse width Tw $\leq$ 0.1msec. Duty ratio $\leq$ 1/10

## ■ Electro-Optical Characteristics (Ta = 25°C)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 20 mA	-	3.7	4.9	V
Reverse Current	I <sub>F</sub>	V <sub>F</sub> = 5 V			10	μA
Radiant Flux	Po	I <sub>F</sub> = 20 mA		2		mW
Viewing Angle	2θ <sub>1/2</sub>	I <sub>F</sub> = 20 mA		30		deg
Peak Wavelength	$\lambda_{p}$	I <sub>F</sub> = 20 mA	380	385	388	nm
Spectrum Radiation Bandwidth	Δλ	$I_F = 20 \text{ mA}$		18		nm



<sup>\*2</sup> Soldering portion of lead: 3mm from bottom face of resin package.